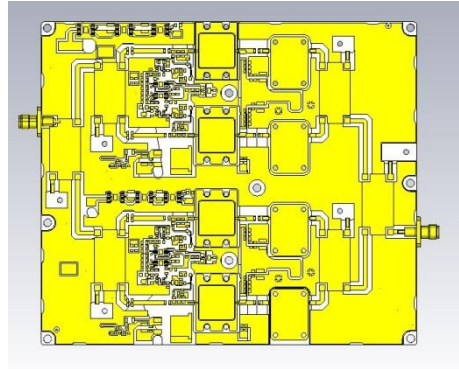


RAP2833P60; 2.8 GHz – 3.3 GHz 1 kW

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Small Dimensions & Light Weight
- Fast Switching Capability



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	2.8-3.3 GHz
Output Power:	1000 W Min. %10 300 μ s
Nominal Gain:	10 dB
Gain Flatness:	\pm 1 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞ :1
DC Supply Voltage:	50 V
Efficiency:	% 45
Enable Speed:	1 μ s max.
Pulse Droop :	0.5 dB
Rise / Fall Time	50 nsec max.
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F, 516.5
Vibration:	MIL-STD-810F, 514.5

INTERFACES

RF Input:	SMA Female
RF Output:	SMA Female
50 V :	Solder Pad
GND :	Solder Pad
Enable :	Solder Pad

MECHANICAL SPECIFICATIONS

Size (mm) :	159.1 x 137.1
(inch) :	6.26 x 5.40
Weight :	gr.
Plating :	Yellow Chromate

